## SPATIAL CORRELATION OF LINEAR AND NONLINEAR ELECTRON TRANSPORT IN A SUPERCONDUCTING MICROWAVE RESONATOR: LASER SCANNING MICROSCOPY ANALYSIS

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Nonlinear (NL) microwave (RF) response of high- $T_C$  superconductors (HTS) at high circulating power limits the applicability of HTS resonators to the few-mW level. *Globally*, the NL response is the integrated contribution of individual *local* sources that are non-uniformly distributed in superconducting elements. Therefore, methods of spatially-resolved RF analysis are needed to identify the NL sources as well as to establish their relative influence on the global response.

Laser scanning microscopy (LSM) has made a good showing as a method for 2-D probing simultaneously the spatial variations of (i) RF current flow,  $J_{RF}(x,y)$ , of (ii) areas of resistive dissipation, and (iii) the sources of microwave NL in operating HTS devices [1]. A brightness contrast in the LSM images is created by photoresponse (PR) signals arising from local overheating of the HTS film with a micron-size laser probe. The intensity of the probe is modulated by a 100 kHz oscillator producing a periodic modification of the shape of the temperature-dependent microwave transmission  $S_{21}(f,T)$  characteristic. At fixed RF frequency, f, and spatially constant temperature oscillation ( $\delta T(x,y)=0.1$  K) in the x,y scanned area of the HTS film, the LSM PR is proportional to the laser-beam-induced changes in resonator transmittance,  $\delta //S_{21}(f)//^2$ , that can be expressed in a form [2]:

$$PR \sim \delta \|S_{12}(f)\|^{2} = \frac{1}{2} \left( \frac{\|S_{12}(f)\|^{2}}{\partial f_{0}} \frac{\partial f_{0}}{\partial T} + \frac{\|S_{12}(f)\|^{2}}{\partial (1/2Q)} \frac{\partial (1/2Q)}{\partial T} + \frac{\|S_{12}(f)\|^{2}}{\partial \widehat{S}_{12}^{2}} \frac{\partial \widehat{S}_{12}^{2}}{\partial T} \right) \delta T(x, y), \tag{1}$$

where the three items in the brackets in (1) symbolize inductive (PR<sub>X</sub>), resistive (PR<sub>R</sub>), and insertion loss (PR<sub>IL</sub>) components of LSM PR, respectively, and  $f_0$  – is the resonant RF frequency, Q – is the quality factor, and  $\hat{S}_{12}$  –is the maximum of the transmission coefficient. Evidently, the PR<sub>X</sub>(x,y) originates from frequency  $\delta f_0$  tuning due to the laser-probe-induced modulation of the HTS kinetic inductance. The effect was used to image a quantity proportional to the square of the local current density  $J_{RF}(x,y)$ . The remaining components PR<sub>R</sub>(x,y) and PR<sub>IL</sub>(x,y) reflect changes in Ohmic dissipation produced by the laser probe and, therefore, were used to image spatial variations of the dissipation by a procedure that is described in detail in [2].

The two-tone method of excitation by two microwave sources having fixed frequencies  $f_{1,2} = f_0 \pm \Delta f/2$  and the same output power  $P_{f1} = P_{f2}$  was applied to image RF properties of the resonator, where  $f_0 = 1.872$  GHz is the frequency of the fundamental resonance at T = 77 K, and  $\Delta f = 0.2$  MHz is the spacing. The zero-span mode of a Spectrum Analyzer was used to detect the probe-induced LSM PR(x,y) at  $f_1$  and  $f_2$  for imaging PR<sub>R</sub>(x,y) and PR<sub>IL</sub>(x,y) in compliance with the partition method described in [2]. The modulation of RF signals

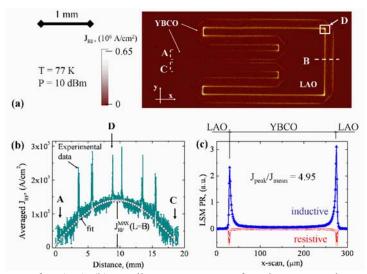


Fig.1. (a) 2-D LSM map of  $J_{RF}(x,y)$ , (b) standing wave pattern of section-averaged RF current density along the length of the strip line, and (c) mid-section profiles of  $PR_X(x)$  and  $PR_R(x)$  at T = 77K, P=10 dBm, and a loaded  $Q_L \sim 1860$ . Brighter areas in (a) correspond to peak values of  $J_{RF}(x,y)$ 

transmitted at  $f=2f_1-f_2$  and at  $f=2f_2-f_1$  intermodulation (IMD) harmonics were used to image the distribution of *microscopic* sources of NL response [3].

Figure 1(a) shows 2-D LSM PR<sub>X</sub>(x,y) image of the HTS device previously characterized by us in [3]. This was a YBa<sub>2</sub>Cu<sub>3</sub>O<sub>y</sub> (YBCO) film with thickness of about 1  $\mu$ m configured by ion-milling lithography on LaAlO<sub>3</sub> (LAO) substrate into a meandering strip line resonator with line width of 250  $\mu$ m. The topology of the resonator is clear from the PR<sub>X</sub>(x,y) map manifesting the predicted peaks of J<sub>RF</sub>(x,y) along the strip edges. Ends of the micro strip are outlined by dotted line in sections A and C in the Fig. 1(a) for clarity. At P = 10 dBm, the PR<sub>X</sub>(x,y) reached a maximum corresponding to J<sub>RF</sub>(x,y) = 6.35\*10<sup>5</sup> A/cm<sup>2</sup> at the position of a corner outlined by the white box D. To be sure that the imaged J<sub>RF</sub>(x,y) in Fig. 1(a) corresponds exactly to the distribution of RF electronic transport in the resonator standing wave pattern, an unfolding of the section-averaged (PR<sub>X</sub>)<sup>1/2</sup> distribution is plotted in Fig. 1(b). As evident, a fit to J<sub>RF</sub>(L)= J<sub>RF</sub><sup>MAX</sup>sin(2 $\pi$ L/L<sub>0</sub>) (L<sub>0</sub> = length of meandering segment from A to C) is almost ideally matched to the measured distribution along the length L of the resonator from A through mid section B to C, showing averaged J<sub>RF</sub>(L=B)=1.3\*10<sup>5</sup> A/cm<sup>2</sup> at the crest of standing wave. This value was used to calibrate the amplitude of PR<sub>X</sub> in J<sub>RF</sub> units. A line-scan profile of the PR<sub>X</sub>(x) distribution

Figure 2(a) shows RF power-dependent modification of the edge profiles of the total LSM PR. A series of profiles was obtained at  $f_1$  (positive PR amplitude, above  $f_0$ ) and at  $f_2$  (negative PR amplitude, below  $f_0$ ) by repeating the same line scan through the corner D in the range of input P from -12dBm to +15 dBm in 1 dBm steps. It was detected that in linear LSM PR mode the photoresponse grows in a nonlinear manner at high P

in section B was used to make such a calibration [1].

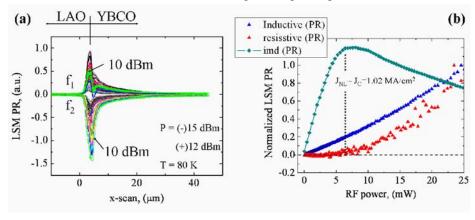


Fig. 2. (a) Detailed profiles of LSM PR(x) through area D obtained at frequencies  $f_1$  and  $f_2$  in the range from -12dBm to +15dBm, and (b) extracted local power dependencies of  $PR_X$ ,  $PR_R$ , and  $PR_{IMD}$ 

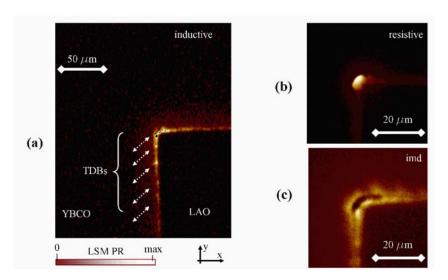


Fig. 3. (a) 2-D LSM images of (a) PR<sub>X</sub>, (b) PR<sub>R</sub>, and (c) PR<sub>IMD</sub> in the vicinity of area D in Fig. 1(a)

starting from 4 mW (~2 dBm). Moreover, the shape of the PR(x,  $f_1$ ) profile was spatially collapsed at P>8 dBm (see the 10 dBm profile in Fig. 2(a)). This is due to the impact of the negative sign of PR<sub>R</sub>(x) at all the frequencies decreasing the amplitude of the total PR in resistive areas at  $f_1$  and increasing it at  $f_2$ . By focusing the laser probe at an arbitrary position on the HTS film in the vicinity of D, we extracted the local values of different components of LSM PR in an area limited by the radius of the thermal healing length ( $l_T$ ~4  $\mu$ m) around the best focus. The normalized power dependencies of those PR<sub>X</sub>, PR<sub>R</sub>, and PR<sub>IMD</sub> are shown in Fig.2 (b). One can see an almost linear growth of PR<sub>X</sub> as a function of increasing input power. In contrast, PR<sub>R</sub> remains zero up to some critical power P<sub>C</sub>~2 mW corresponding to J<sub>C</sub>(D)=1.02 MA/cm² and then starts its NL behavior for J<sub>RF</sub>(D)>J<sub>C</sub>(D). This feature correlates well with the power dependence of NL (PR<sub>IMD</sub>) components, perhaps showing an interconnection of J<sub>C</sub>(D) and the NL current density scale, J<sub>NL</sub>(D). However, the onset of PR<sub>R</sub>(P) here produces a maximum in the PR<sub>IMD</sub>(P) dependence that may result from a decreasing of the relative portion of superfluid component in the total J<sub>RF</sub> due to depairing, with J<sub>NL</sub>~1 MA/cm² at the corner D. The effect of Cooper depairing is spatially dependent since it is directly determined by both the topology of J<sub>RF</sub>(x,y) and the superconducting gap distribution at defects of the HTS microstructure and patterned edges, as well as local doping.

Figure 3(a) shows a 200 x 250  $\mu$ m<sup>2</sup> area scan of PR<sub>X</sub>(x,y) in region D. Spatial modulation of PR<sub>X</sub>(x,y) is obvious here owing to the highest J<sub>RF</sub>(x,y) along the microstrip edges and due to variations of magnetic penetration depth at low-angle grain-boundaries (GBs) formed at interfaces of individual twin-domain blocks (TDBs). The direction and position of some TDBs are marked by double-arrow lines in the Fig. 3(a). Those TDBs (retracing the surface structure of the LAO substrate) were identified independently by the LSM operating in the reflection mode of a light microscope. Additionally, a detailed PR<sub>R</sub>(x,y) image is shown in Fig. 3(b). The distinguishing feature of this image is that the edge inhomogeneities of PR<sub>R</sub>(x,y) are obscured by the very large LSM PR just at the corner D, resulting from exponential growth of local current-voltage steepness from J<sub>RF</sub>(x,y). In this area the maximum of J<sub>RF</sub>(x,y) may be creating an overcritical state of the HTS film leading to a more linear (normal-metal like) behavior of the local NL sources that is seen as a black (zero-response) zone in the IMD image [see Fig. 3(c)]. In contrast, the remaining critical-state regions give a maximum value to the J<sub>IMD</sub>(x,y) signal as evident from Fig. 3(c).

## References

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